SYSTEMS AND DEVICES INCLUDING FIN TRANSISTORS AND METHODS OF USING, MAKING, AND OPERATING THE SAME

Abstract

Disclosed are methods, systems and devices, including a system, having a memory device. In some embodiments, the memory device includes a plurality of fin field-effect transistors (190) disposed in rows (164), a plurality of insulating fins (154) each disposed between the rows (164), and a plurality of memory elements each coupled to a terminal (192, 194) of a fin field-effect transistor (190) among the plurality of fin field-effect transistors (190).

FIG. 21